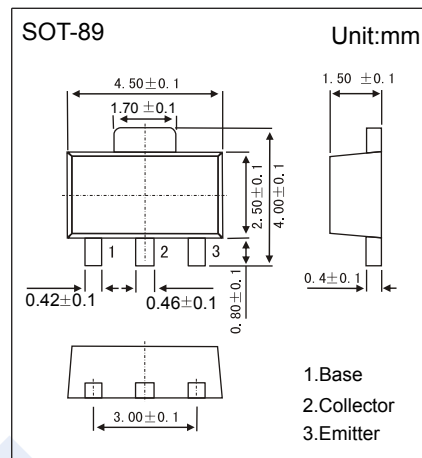


PNP Transistors

2SA1896

■ Features

- Collector Current Capability $I_C = -2.5A$
- Collector Emitter Voltage $V_{CE0} = -20V$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-25	V
Collector - Emitter Voltage	V_{CE0}	-20	
Emitter - Base Voltage	V_{EB0}	-7	
Collector Current - Continuous	I_C	-2.5	A
Collector Current - Pulse	I_{CP}	-5	
Collector Power Dissipation (Note.1)	P_C	1.3	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: Mounted on ceramic substrate ($250mm^2 \times 0.8mm^1$)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu A, I_E = 0$	-25			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 mA, R_{BE} = \infty$	-20			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_C = 0$	-7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20 V, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5 A, I_B = -30mA$			-0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1.5 A, I_B = -30mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -0.5A$	140		400	
		$V_{CE} = -2V, I_C = -2.5A$	70			
Collector output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		26		pF
Transition frequency	f_T	$V_{CE} = -2V, I_C = -0.3A$		400		MHz

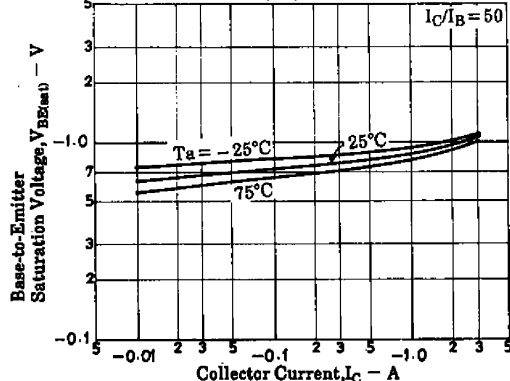
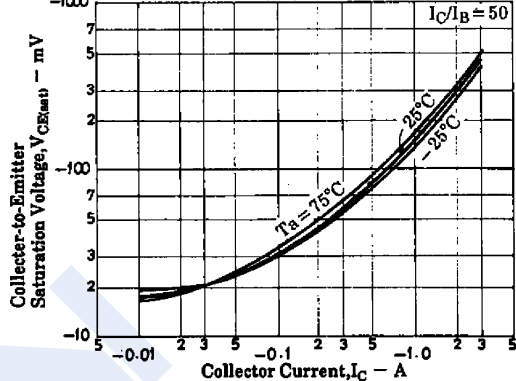
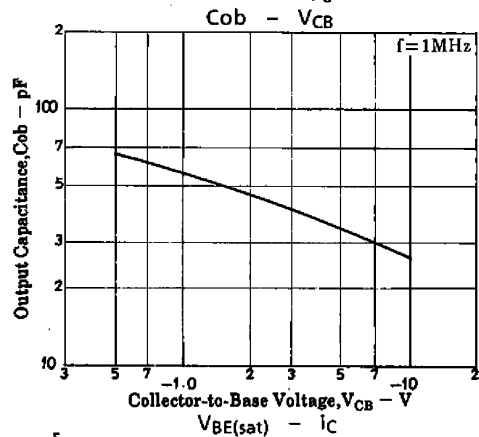
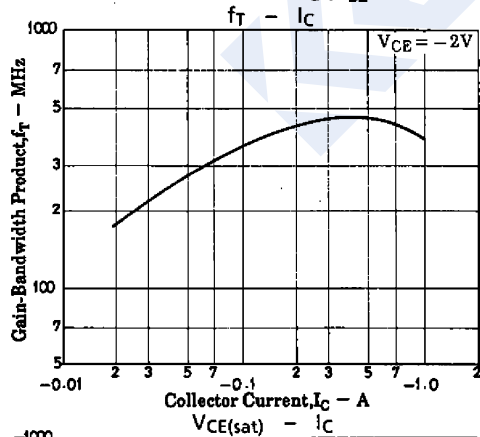
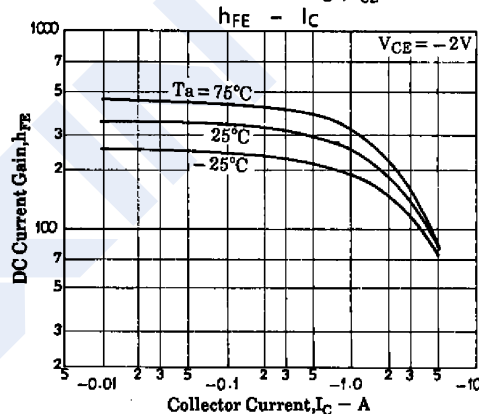
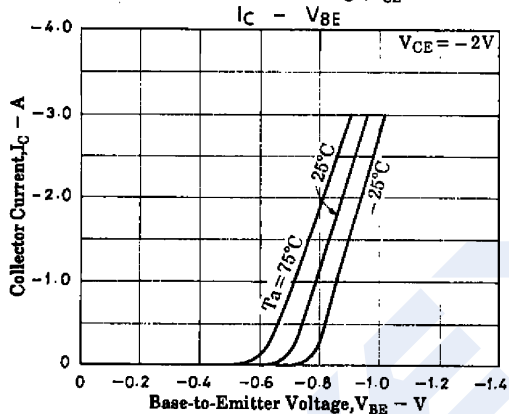
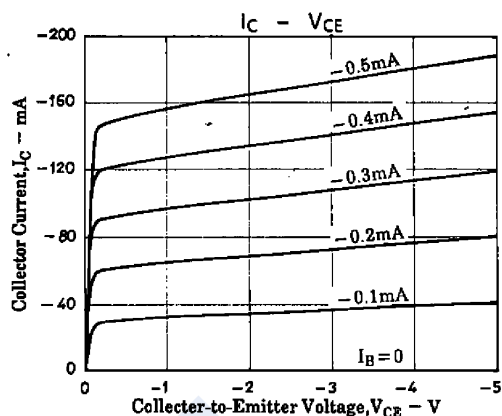
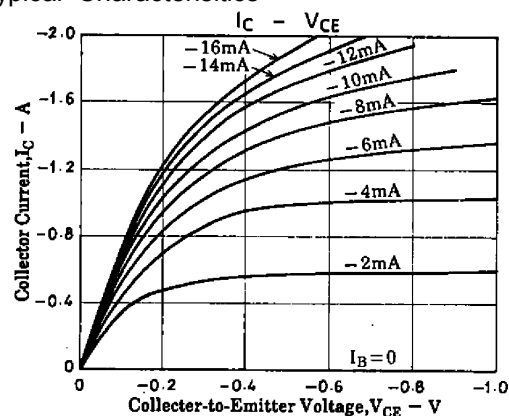
■ Classification of $h_{FE}(1)$

Type	2SA1896-S	2SA1896-T
Range	140-280	200-400
Marking	AM S*	AM T*

PNP Transistors

2SA1896

■ Typical Characteristics



PNP Transistors

2SA1896

■ Typical Characteristics

